

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-13. Canceled.

14. (New): A high-frequency circuit for branching high-frequency signals for pluralities of communications systems of different frequencies, which comprises:

a lowpass filter circuit disposed between first and second ports and/or a highpass filter circuit disposed between said first port and a fourth port; and

a matching circuit and a bandpass filter circuit disposed between said first port and a third port;

said matching circuit having an inductance element disposed between said first port and ground, and a capacitance element disposed between said first port and said bandpass filter circuit;

said bandpass filter circuit being a SAW filter;

the passband f_1 of said lowpass filter circuit, the passband f_2 of said bandpass filter circuit, and the passband f_3 of said highpass filter circuit meeting the condition of $f_1 < f_2 < f_3$;

said lowpass filter circuit having a parallel resonance circuit comprising an inductance element and a capacitance element, said parallel resonance circuit having a resonance frequency within the passband f_2 of said bandpass filter circuit;

said highpass filter circuit having a series resonance circuit comprising an inductance element and a capacitance element, said series resonance circuit having a resonance frequency within the passband f_2 of said bandpass filter circuit.

15. (New): The high-frequency circuit according to claim 14, wherein said inductance element disposed between said first port and ground has a Q value of 20 or more at 250 MHz to absorb electrostatic surge.

16. (New): The high-frequency circuit according to claim 14, wherein said inductance element of said series resonance circuit has a Q value of 20 or more at 250 MHz.

17. (New): The high-frequency circuit according to claim 14, wherein said second to fourth ports are connected to an amplifier circuit,

wherein a switch circuit comprising a switching element is disposed between said fourth port and said amplifier circuit, and

wherein a bandpass filter circuit and a balanced-unbalanced circuit are disposed between said switch circuit and said amplifier circuit.

18. (New): The high-frequency circuit according to claim 14, wherein said SAW filter comprises a balanced port connected to said third port, and an unbalanced port connected to said first port.

19. (New): The high-frequency circuit according to claim 18, wherein a matching circuit comprising an inductance element and/or a capacitance element is connected to the balanced port of said SAW filter.

20. (New): The high-frequency circuit according to claim 14, wherein said first port is connected to a multi-band antenna.

21. (New): A high-frequency device comprising
a lowpass filter circuit disposed between a first port and a second port and/or a highpass filter circuit disposed between said first port and a fourth port; and

a matching circuit and a bandpass filter circuit disposed between said first port and a third port;

said matching circuit having an inductance element disposed between said first port and ground, and a capacitance element disposed between said first port and said bandpass filter circuit;

said bandpass filter circuit being a SAW filter;

the passband f_1 of said lowpass filter circuit, the passband f_2 of said bandpass filter circuit, and the passband f_3 of said highpass filter circuit meeting the condition of $f_1 < f_2 < f_3$;

said lowpass filter circuit having a parallel resonance circuit comprising an inductance element and a capacitance element, said parallel resonance circuit having a resonance frequency within the passband f_2 of said bandpass filter circuit;

at least part of circuit elements (inductance elements and capacitance elements) constituting said highpass filter circuit, said lowpass filter circuit and said matching circuit being

formed by electrode patterns and contained in a laminate substrate, and the remaining circuit elements and a SAW filter being mounted onto said laminate substrate.

22. (New): The high-frequency device according to claim 21, wherein electrode patterns constituting the inductance element and the capacitance element of said highpass filter circuit, electrode patterns constituting the inductance element and the capacitance element of said lowpass filter circuit, and electrode patterns constituting the inductance element and the capacitance element of said matching circuit are disposed, such that they do not overlap each other in a lamination direction of said laminate substrate.

23. (New): The high-frequency device according to claim 21, wherein the capacitance element and the inductance element constituting said matching circuit are mounted onto said laminate substrate.

24. (New): The high-frequency device according to claim 23, wherein said inductance element for said matching circuit comprises a core having a leg at each end, a coil wound around said core, and a terminal electrode disposed on the lower side of said leg and connected to an end of said coil, said core being made of a non-magnetic, alumina-based ceramic material.

25. (New): The high-frequency device according to claim 21, wherein a ground electrode is formed substantially on an entire surface of a layer close to a mounting surface of said laminate substrate to prevent interference with a mounting substrate, and LGA (land grid

array) terminal electrodes are formed on the mounting surface of said laminate substrate, said terminal electrodes being connected to each filter through via-holes.